

Features

- Attenuation: 1 dB steps to 50 dB
- Temperature Stability: ± 0.18 dB from -40°C to $+85^{\circ}\text{C}$ Typical
- Low DC Power Consumption
- Surface Mount Package
- Integral TTL Driver
- High Intercept Point
- Low Cost/High Performance
- 50 Ohm Nominal Impedance
- Lead-Free CR-13 Package
- 260°C Reflow Compatible
- RoHS* Compliant

Description

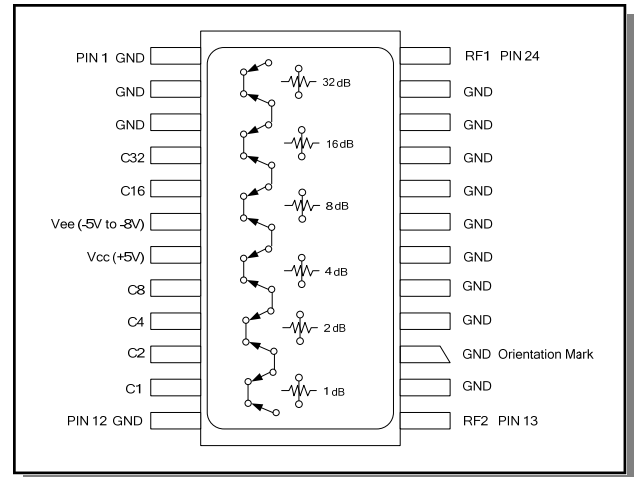
M/A-COM's AT20-0106 is a GaAs FET 6-bit digital attenuator with a 1 dB minimum step size and 50 dB total attenuation. This attenuator and integral TTL driver is in a ceramic 24-lead surface mount package. The AT20-0106 is ideally suited for use where accuracy, fast switching, low power consumption and low intermodulation products are required. Typical applications include dynamic range setting in precision receiver circuits and other gain/leveling control circuits. Available with enhanced performance as fully hermetic version. Environmentally screenable as P/N AT-106-PIN.

Ordering Information

Part Number	Package
AT20-0106-PIN	Bulk Packaging
AT20-0106-TR	1000 piece reel
AT20-0106-TB	Sample Test Board

Note: Reference Application Note M513 for reel size information.

Functional Schematic



Pin Configuration

Pin No.	Function	Pin No.	Function
1	GND	13	RF2
2	GND	14	GND
3	GND	15	GND
4	C32	16	GND
5	C16	17	GND
6	Vee (-5V to -8V)	18	GND
7	Vcc (+5V)	19	GND
8	C8	20	GND
9	C4	21	GND
10	C2	22	GND
11	C1	23	GND
12	GND	24	RF1

The metal bottom of the case must be connected to RF and DC ground.

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

Electrical Specifications: $T_A = 25^\circ\text{C}^1$

Parameter	Test Conditions	Frequency	Units	Min	Typ	Max
Reference Insertion Loss	—	DC - 0.5 GHz	dB	—	3.5	3.8
		DC - 1.0 GHz	dB	—	3.9	4.2
		DC - 2.0 GHz	dB	—	4.2	4.6
Attenuation Accuracy ²	Any Single Bit Any Combination of Bits (For attenuation to 26 dB) Any Combination of Bits (For attenuation 27 to 50 dB)	DC - 2.0 GHz	dB	± (0.3 +4% of atten. setting)		
		DC - 2.0 GHz	dB	± (0.4 +4% of atten. setting)		
		DC - 1.5 GHz	dB	± (0.5 +5% of atten. setting)		
VSWR	—	0.05 - 0.10 GHz 0.101 - 2.0 GHz	Ratio Ratio	— —	— —	2.0:1 1.8:1
Trise, Tfall	10% to 90%	—	ns	—	—	50
Ton, Toff	50% Control to 90/10% RF	—	ns	—	—	150
Transients	In-Band (peak-peak)	—	mV	—	50	—
1 dB Compression	Input Power Input Power	0.05 GHz	dBm	—	+20	—
		0.5 - 2.0 GHz	dBm	—	+28	—
Input IP3	For two-tone Input Power Up to +5 dBm	0.05 GHz	dBm	—	+34	—
		0.5 - 2.0 GHz	dBm	—	+46	—
Input IP2	For two-tone Input Power Up to +5 dBm	0.05 GHz	dBm	—	+45	—
		0.5 - 2.0 GHz	dBm	—	+79	—
Vcc	—	—	V	4.5	5.0	5.5
Vee	—	—	V	-8.0	—	-5.0
Icc	Vcc = 4.5 to 5.5V Vctl = 0 to 0.8V, or Vcc – 2.1V to Vcc	—	mA	—	—	6.0
Iee	Vee = -5.0 to -8.0V	—	mA	—	—	1.0

1. All specifications apply when operated with bias voltages of +5V for Vcc and –5.0V for Vee.
2. This attenuator is guaranteed monotonic.

Absolute Maximum Ratings ^{3,4}

Parameter	Absolute Maximum
Max Input Power 0.05 GHz 0.5 - 2.0 GHz	+27 dBm +34 dBm
V_{CC}	$-0.5V \leq V_{CC} \leq +7.0V$
V_{EE}	$-8.5V \leq V_{EE} \leq +0.5V$
$V_{CC} - V_{EE}$	$-0.5V \leq V_{CC} - V_{EE} \leq 14.5V$
V_{in}^5	$-0.5V \leq V_{in} \leq V_{CC} + 0.5V$
Operating Temperature	$-40^{\circ}C$ to $+125^{\circ}C$
Storage Temperature	$-65^{\circ}C$ to $+150^{\circ}C$

- Exceeding any one or combination of these limits may cause permanent damage to this device.
- M/A-COM does not recommend sustained operation near these survivability limits.
- Standard CMOS TTL interface, latch-up will occur if logic signal is applied prior to power supply.

Handling Procedures

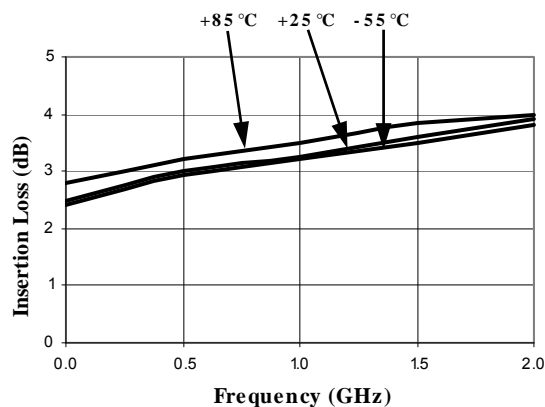
Please observe the following precautions to avoid damage:

Static Sensitivity

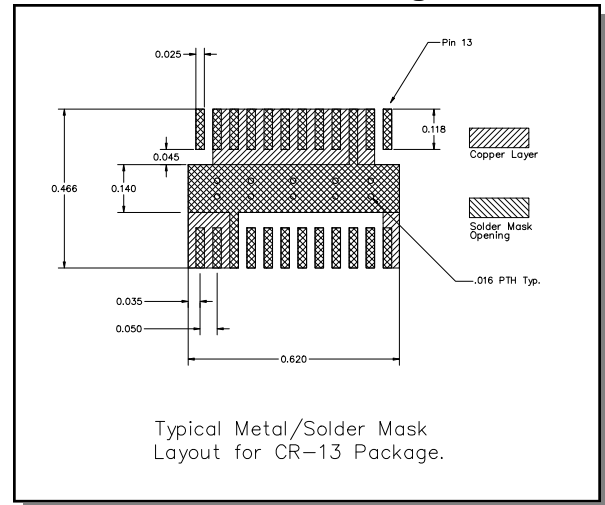
Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

Typical Performance Curves

Insertion Loss vs. Frequency



Recommended PCB Configuration

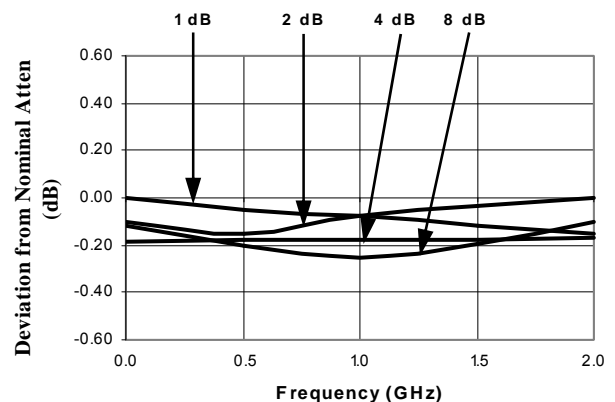


Truth Table (Digital Attenuator)

Control Inputs						Attenuation
C6	C5	C4	C3	C2	C1	
0	0	0	0	0	0	Reference
0	0	0	0	0	1	1 dB
0	0	0	0	1	0	2 dB
0	0	0	1	0	0	4 dB
0	0	1	0	0	0	8 dB
0	1	0	0	0	0	16 dB
1	0	0	0	0	0	32 dB
1	1	1	1	1	1	63 dB

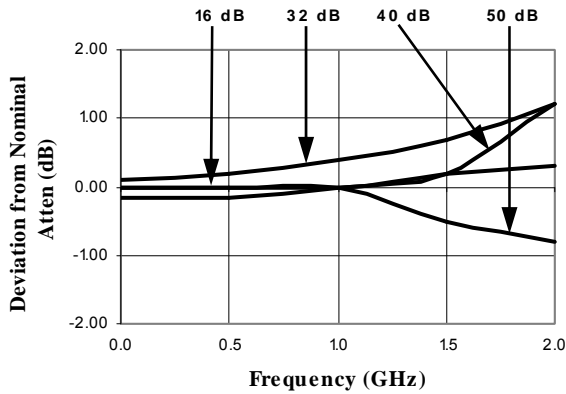
0 = TTL Low; 1 = TTL High

Attenuation Accuracy vs. Frequency

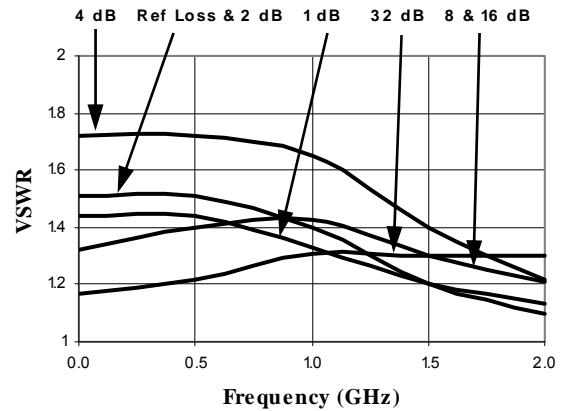


Typical Performance Curves

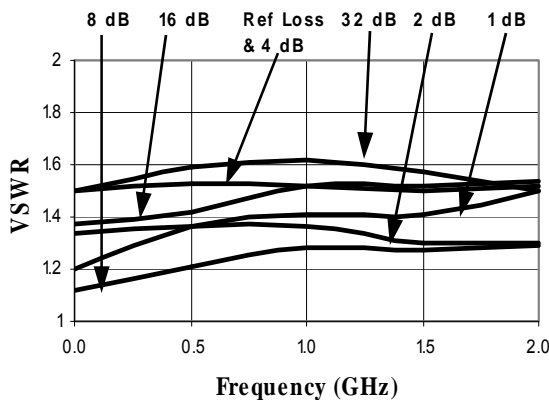
Attenuation Accuracy vs. Frequency



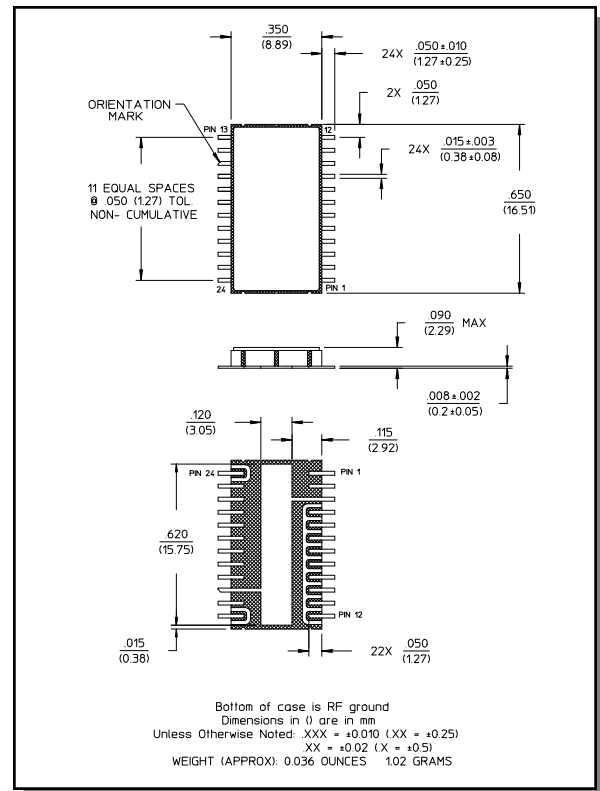
RF1 VSWR vs. Frequency



RF2 VSWR vs. Frequency



Lead-Free, CR-13 Ceramic Package[†]



[†] Reference Application Note M538 for lead-free solder reflow recommendations.

Данный компонент на территории Российской Федерации

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Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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